

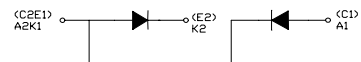
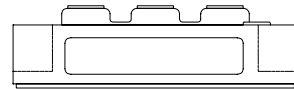
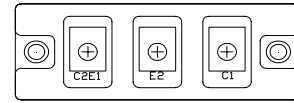
FRD MODULE 100A/1200V/trr:250nsec

PD100F12

OUTLINE DRAWING

FEATURES

- * Isolated Base
- * Dual Diode Doubler Circuit
- * Ultra Fast Recovery
- * High Surge Capability
- * UL Recognized, File No. E187184



TYPICAL APPLICATIONS

- * High Frequency Rectification

Maximum Ratings

Approx Net Weight:210g

Voltage Rating	Symbol	PD100F12		Unit
Repetitive Peak Reverse Voltage per Arm	V_{RRM}	1200		V
Electrical Rating		Condition	Rating	
Average Rectified Output Current	I_o	50Hz Half Sine Wave condition per Arm $T_c=60^\circ\text{C}$	100	A
RMS Forward Current	$I_{F(RMS)}$	per Arm	157	A
Surge Forward Current	I_{FSM}	50 Hz Half Sine Wave, 1 cycle Non-repetitive per Arm	1000	A
I Squared t	I^2t	2 msec to 10 msec per Arm	5000	A^2s
Operating Junction Temperature Range	T_{jw}		-40 to +150	$^\circ\text{C}$
Storage Temperature Range	T_{stg}		-40 to +125	$^\circ\text{C}$
Isolation Voltage	Viso	Base Plate to Terminal, AC1min	2500	V
Mounting torque	Ftor	Case mounting(recommended)	2.8	N.m
		Terminal Screw(recommended)	2.8	

Electrical • Thermal Characteristics

Characteristics	Symbol	Test Conditions	Max.	Unit
Peak Forward Voltage	V_{FM}	$I_{FM}= 100\text{A}$, $T_j=25^\circ\text{C}$, per Arm	2.60	V
Peak Reverse Current	I_{RM}	$V_{RM}= V_{RRM}$, $T_j= 150^\circ\text{C}$, per Arm	20	mA
Reverse Recovery Time	trr	$I_{FM}= 10\text{A}$, $-di/dt= 50 \text{ A}/\mu\text{s}$, $T_a= 25^\circ\text{C}$ Per Arm	250	ns
Thermal Resistance	Rth(j-c)	Junction to Case per Arm	0.28	$^\circ\text{C}/\text{W}$
	Rth(c-f)	Base Plate to Heat Sink with Thermal Compound	0.1	
Internal Lead Inductance	Ls	Anode Terminal to Cathode Terminal Per Element	30	nH

PD100F12 OUTLINE DRAWING (Dimensions in mm)

